

Amendments to the Specification

Please amend the title as follows:

**METHOD OF MANUFACTURING FLIP-CHIP LIGHT EMITTING DIODE
INCLUDING SUBSTRATE REMOVAL**

Please amend the paragraph beginning at page 8 line 9 as follows:

With reference to FIGURE 5, after flip-chip bonding, the GaAs substrate 12' is removed by chemical etching, plasma etching, or another suitable technique. Removal of the epitaxy substrate 12' exposes the n-type AlInGaP layer 16' and a surface of the n-type electrode 32' where it had contacted the substrate 12'. Removal of the GaAs substrate 12' effects a physical separation of the mesas mesa 24' at the ~~trenches~~ trench 26'. If there are a plurality of mesas on the substrate 12', then the removal of the GaAs substrate 12' from the mesas will effect a physical separation of the mesas from one another. After removal of the epitaxy substrate 12', a substantially electrically conductive and light-transmissive window layer 14' is deposited over the n-type AlInGaP layer 16' and the exposed surface of the n-type electrode 32' to form an electrically conductive connection therebetween.